

Oxide Multilayers

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Oxide Multilayers

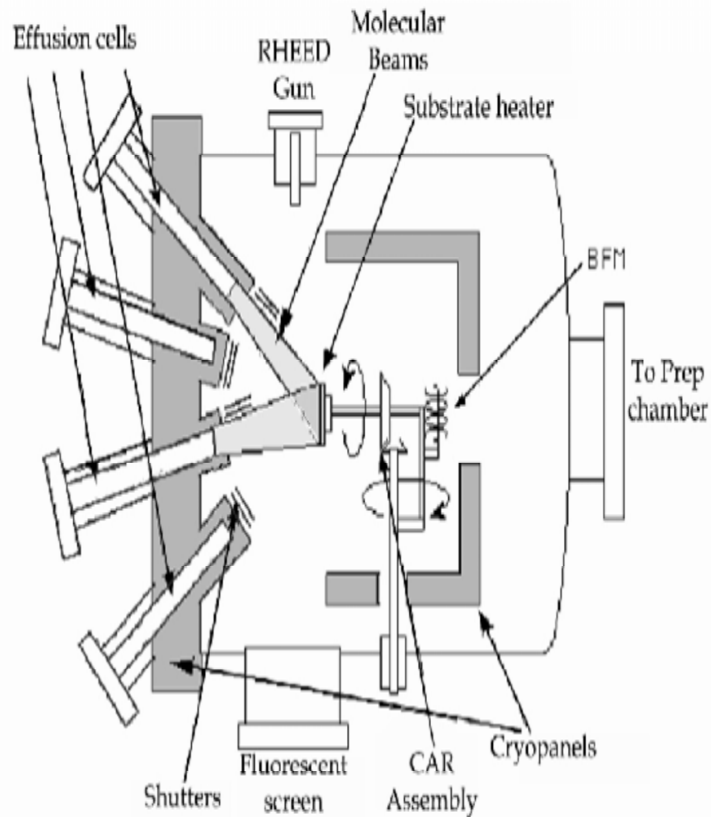
- Multilayer Thin Films
 - Wide range of applications (coating to Laser Diodes)
 - Developing deposition techniques
- Complex Oxides
 - Novel Properties

Outline

- Deposition Techniques
 - Molecular Beam Epitaxy
 - Pulsed-Laser Deposition
 - Reflection High-Energy Electron Diffraction
- Recent Studies
 - Perovskite Oxides
 - Lattice Structure and Electronic Structure
 - Superconductor-Ferroelectric Multilayers

Deposition Techniques

Molecular Beam Epitaxy



– MBE

- can produce high-quality layers with very abrupt interfaces
- Provides good control of thickness, doping, and composition

– ‘Molecular Beams’

- typically from thermally evaporated elemental sources
- deposited onto a heated crystalline substrate to form thin epitaxial layers

Molecular Beam Epitaxy

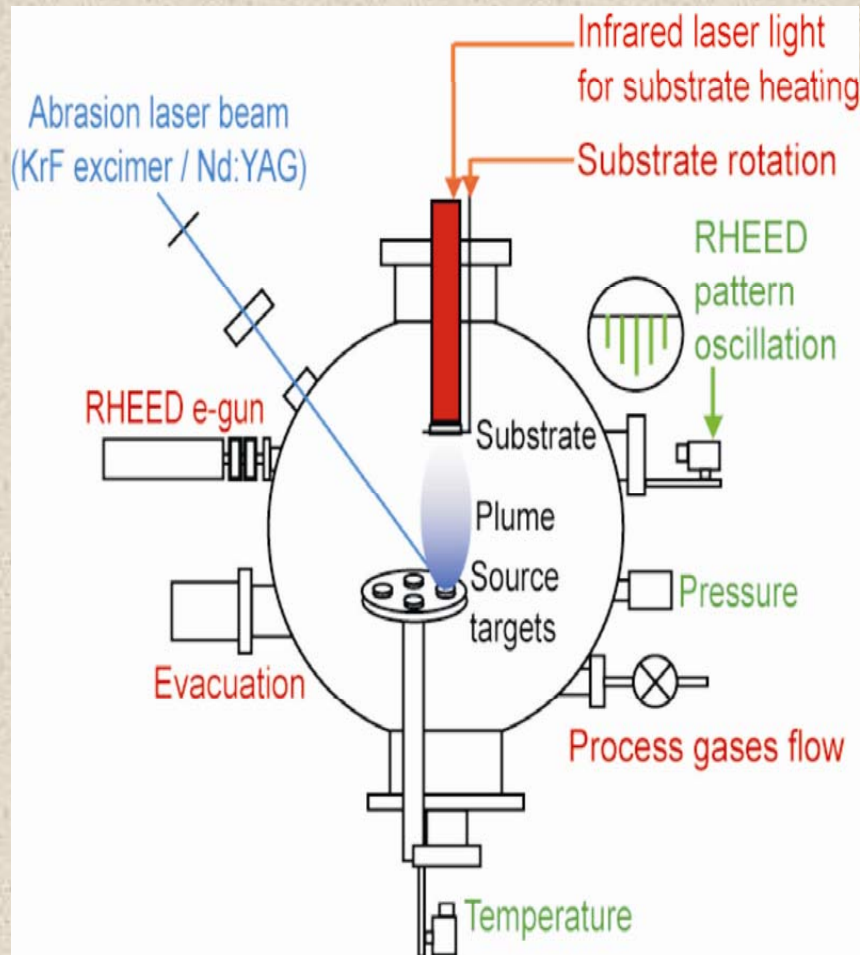


- To obtain high-purity layers
 - extremely pure material sources
 - ultra-high vacuum (10^{-8} Pa)
 - Very fast shutters
 - Very slow growth rates (1 nm/s)



- Very expensive process
- Not suitable for mass production

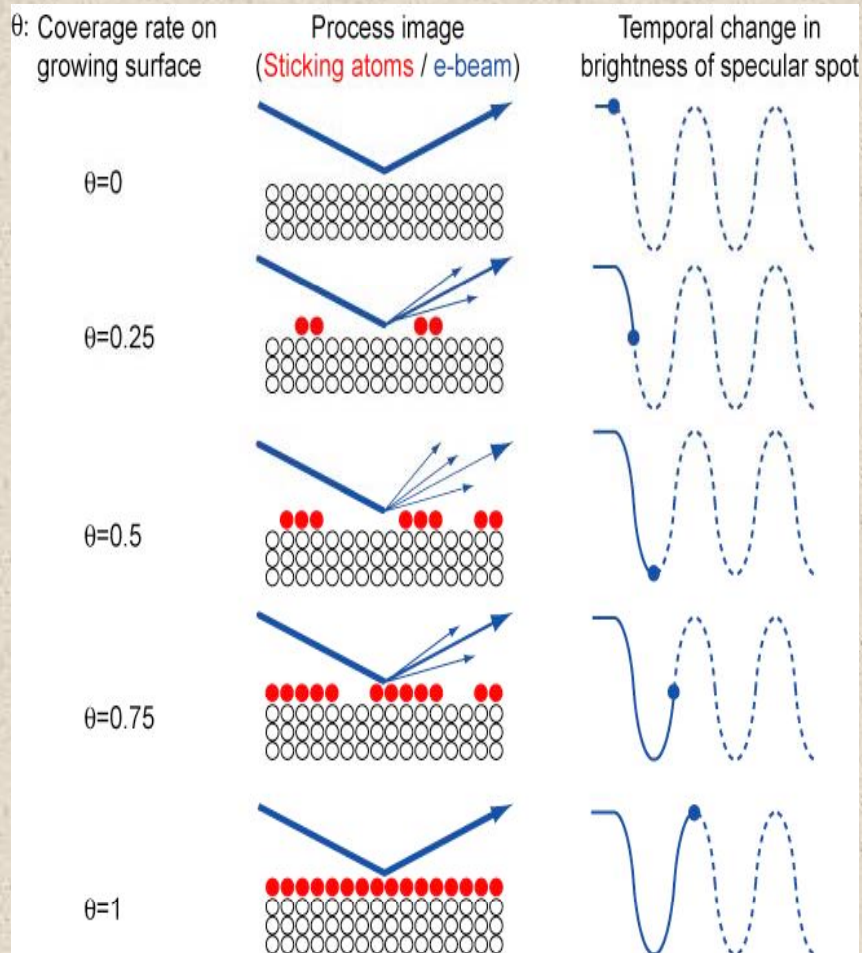
Pulsed-Laser Deposition



– PLD

- The laser-induced expulsion produces a plume of material with stoichiometry similar to the target
- Allows the deposition of multi-element oxides

Reflection High-Energy Electron Diffraction



– RHEED

- is based on the reflection of electrons

With

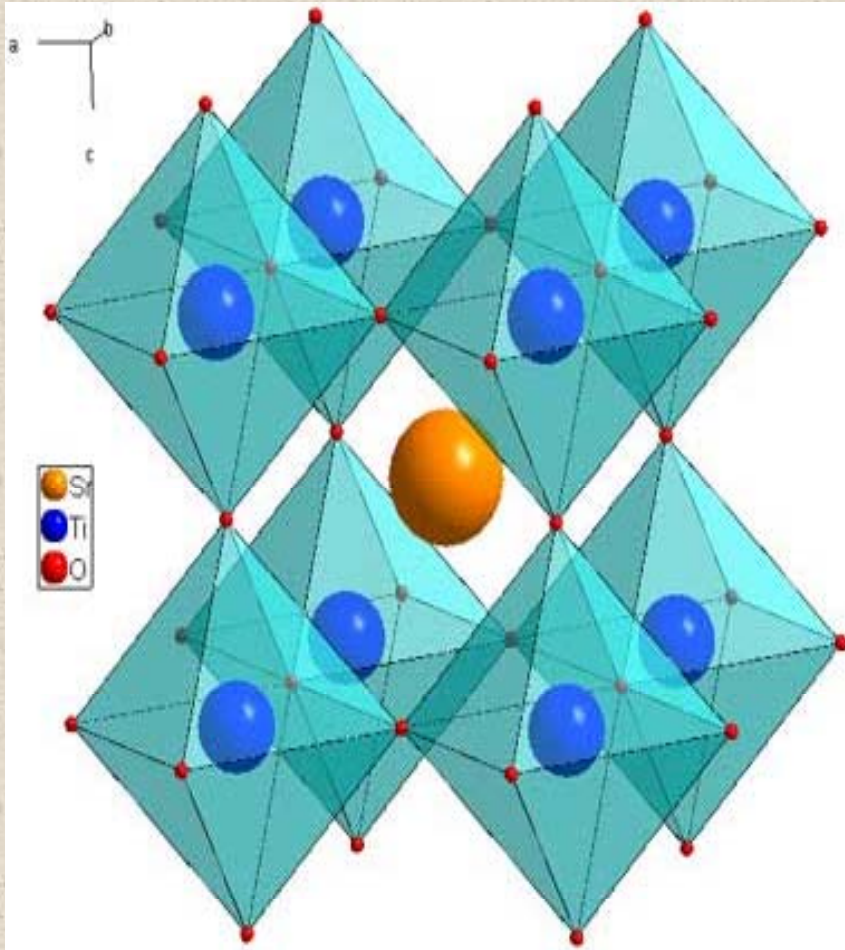
high kinetic energy (5-100 keV)

low impact angle (less than 5°)

- **Intensity** depends on the film roughness
- **Patterns** are used to determine the crystal structure

Recent Studies

Perovskite Oxides

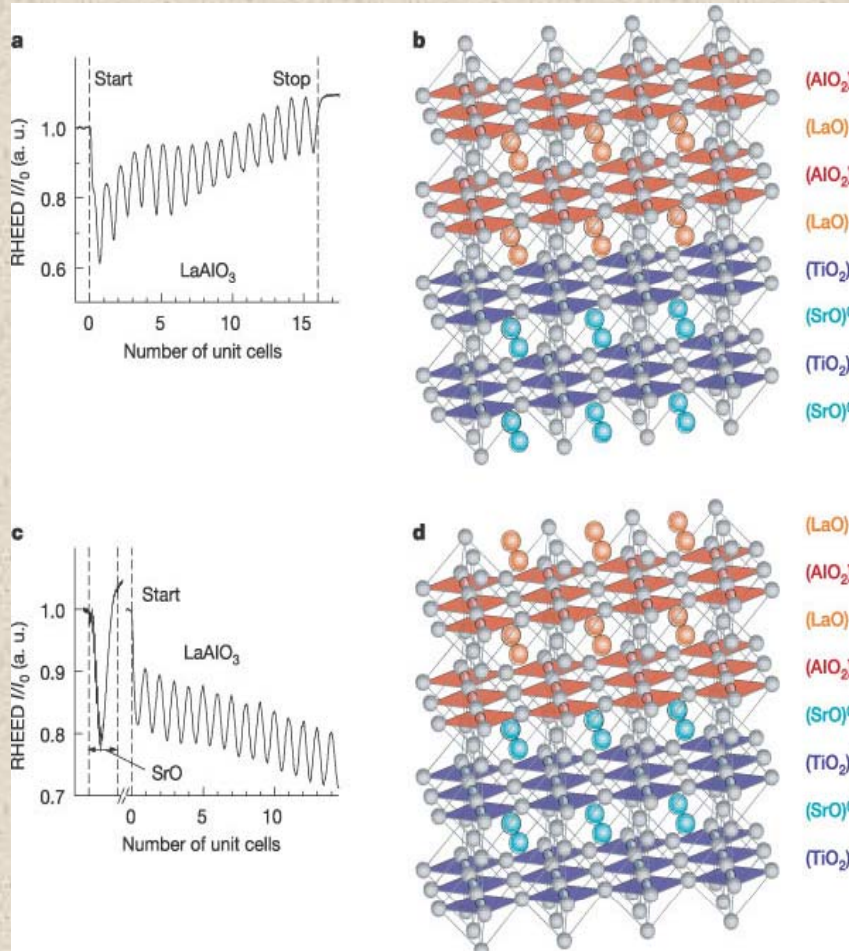


- *Lattice constants*
 - $\text{LaAlO}_3 \sim 3.789\text{\AA}$
 - $\text{SrTiO}_3 \sim 3.905\text{\AA}$
 - $\text{LaTiO}_3 \sim 3.97\text{\AA}$
- *Bandgap*
 - $\text{LaAlO}_3 \sim 5.6\text{ eV}$
 - $\text{SrTiO}_3 \sim 3.2\text{ eV}$



Insulators

$LaAlO_3/SrTiO_3$ superlattice films

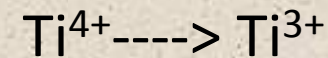
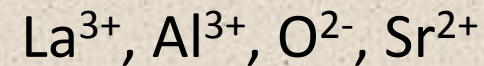


– dangling bonds and incomplete atomic coordination

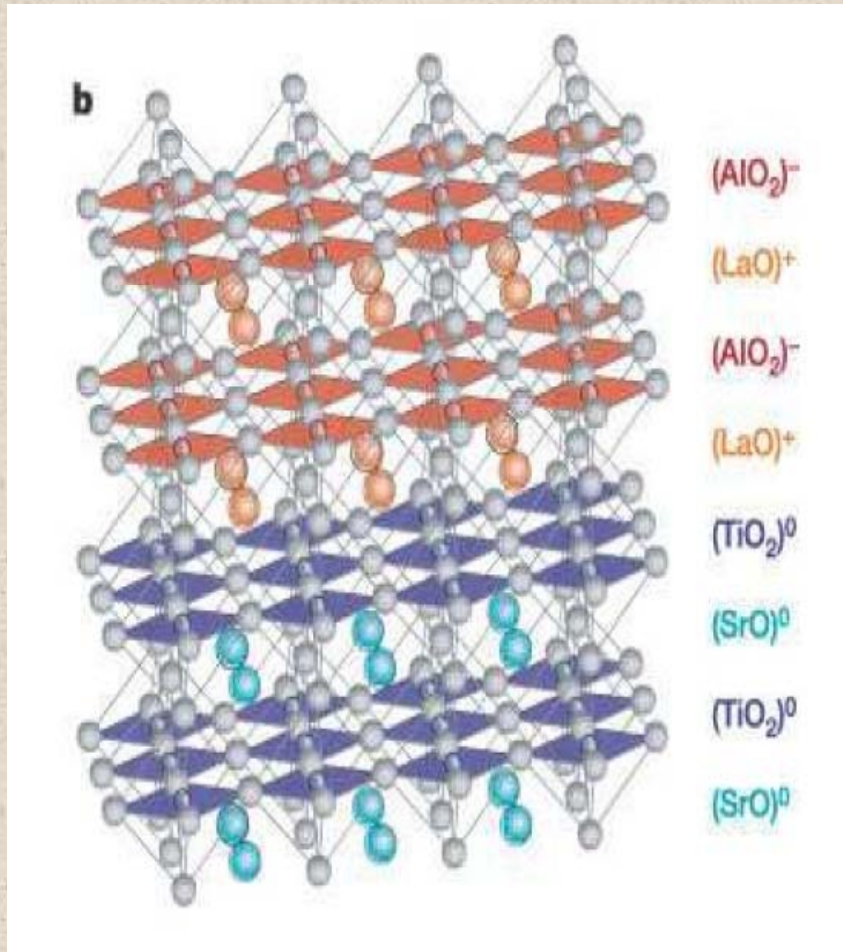


– nontrivial electronic structure at the interface

– Formal valance states

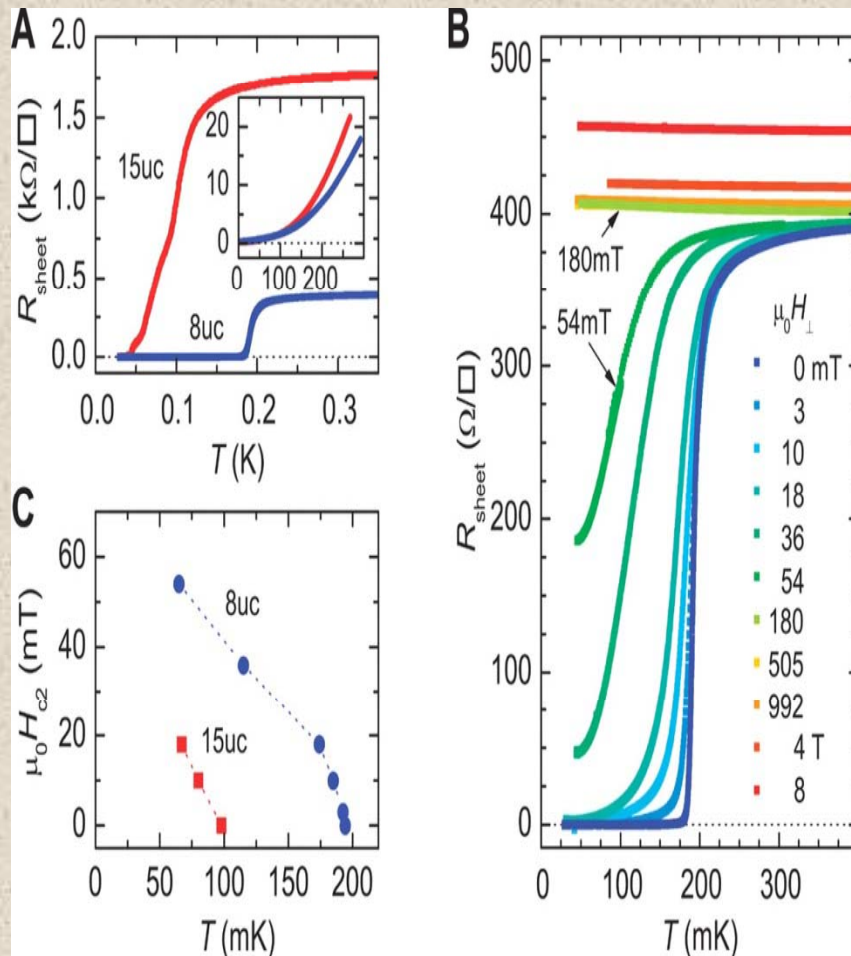


$LaAlO_3/SrTiO_3$ superlattice films



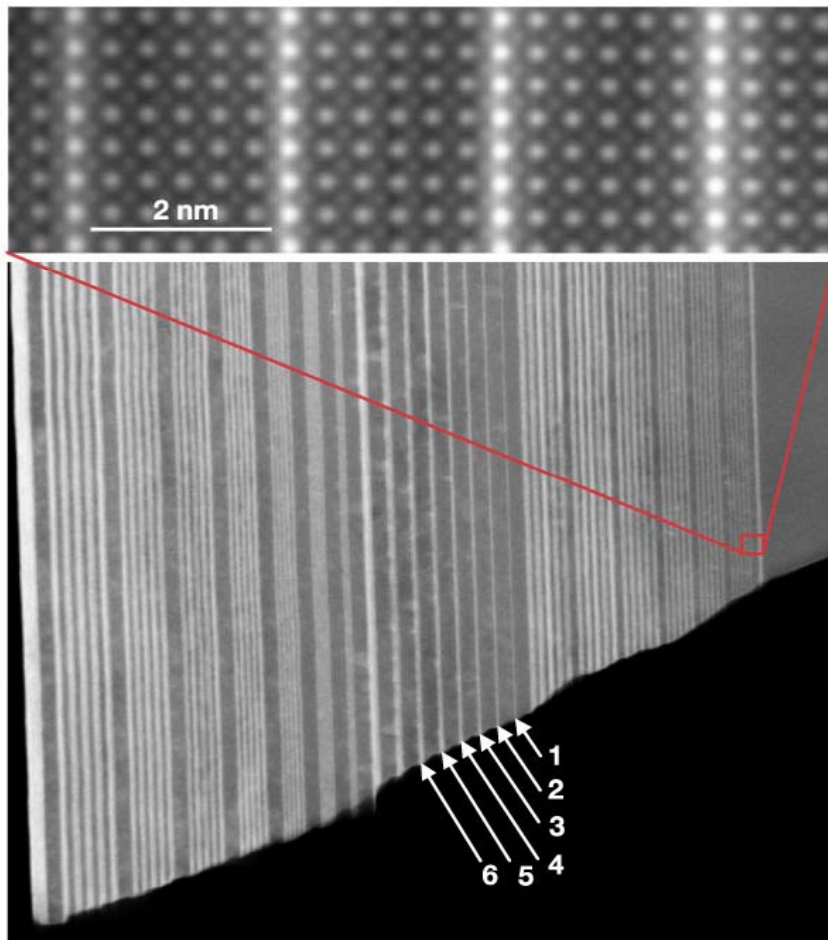
- $SrTiO_3$
 - is a sequence of charge neutral sheets
- $LaAlO_3$
 - alternates between $\pm e$ charged sheets

$LaAlO_3/SrTiO_3$ superlattice films



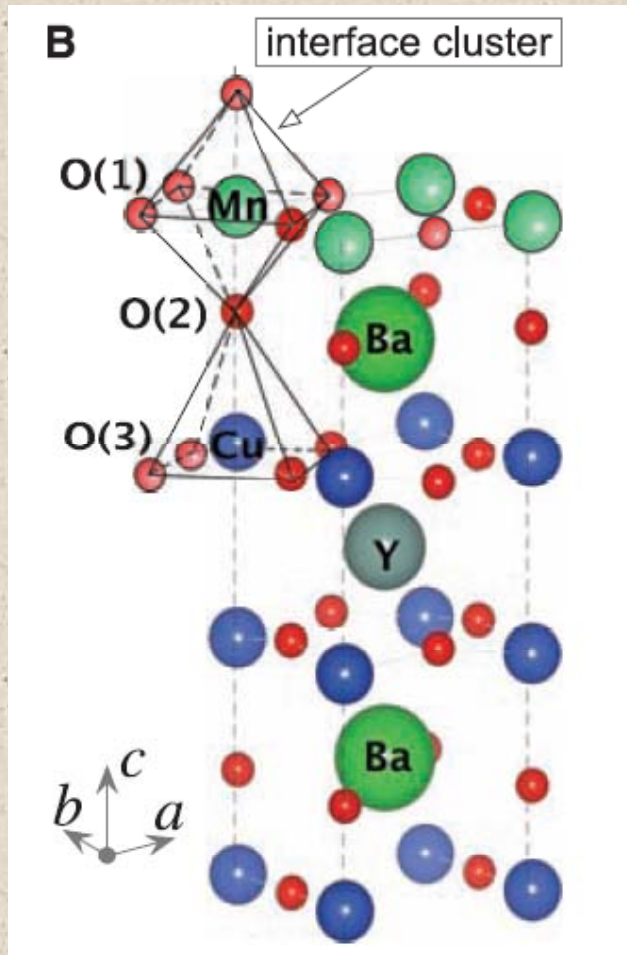
- Ohtomo et al. (2004)
 - interface has a very high carrier mobility exceeding $10,000 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$
- Thiel et al. (2006)
 - large electric-field response
- Reyren et al. (2007)
 - superconductivity in this electron gas with a transition temperature of 200mK

$LaAlO_3/SrTiO_3$ superlattice films



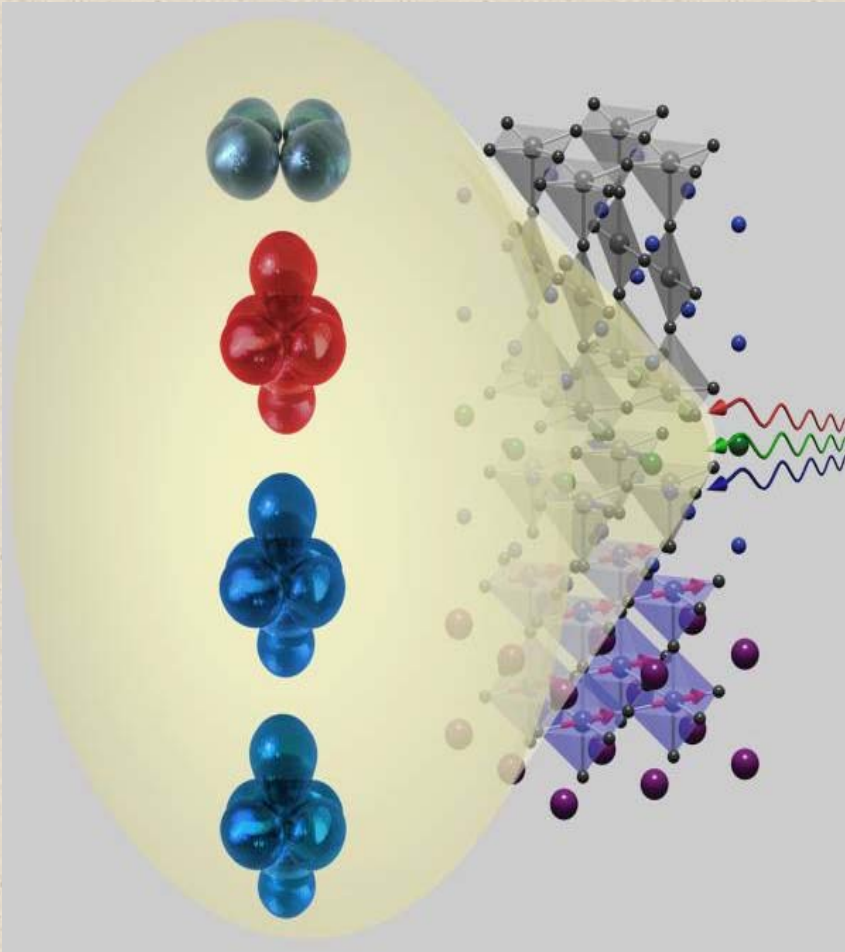
- Ohtomo et al. (2002)
 - spatial distribution of the extra electron in the titanium sites results in metallic conductivity in the interface
 - electron gas is confined within a ~ 2 -nm thick layer

Superconductor-Ferroelectric Multilayers



- Chakhalian et al. (2007)
 - $\text{La}_{0.67}\text{Ca}_{0.33}\text{MnO}_3 / (\text{Y,Ca})\text{Ba}_2\text{Cu}_3\text{O}_7$
 - holes which are constrained to the $\text{Cu } d_{x^2-y^2}$ orbital in the bulk, occupy the $d_{3z^2-r^2}$ orbital at the interface
- orbital reconstruction

Resonant x-ray spectroscopy



- synchrotron sources
 - can create x-rays with tunable energy and polarization
- intra-ionic transition
 - $2p^63d^9 \rightarrow 2p^53d^{10}$ (913eV)
 - polarizations parallel or perpendicular to the interface can be used to observe shifts in the absorption peak

Conclusion

- “Oxide Multilayers” is a relatively new and interesting field
- Since strongly correlated electron materials have very few common points compared to semiconductors their properties are material based and can not be generalized.
- Developing production and diagnostic methods can lead to new novel properties in these structures

References

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